



TO-92 Plastic-Encapsulate Transistors

BF370 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 0.5 W ($T_{amb}=25^{\circ}C$)

Collector current

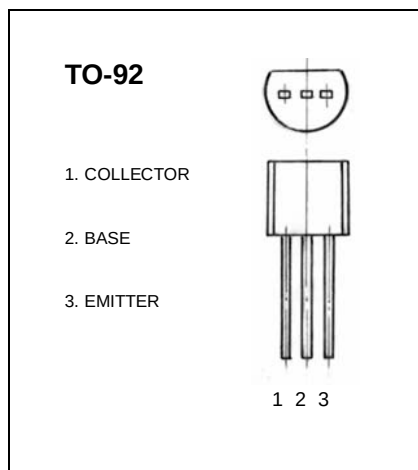
I_{CM} : 0.1 A

Collector-base voltage

$V_{(BR)CBO}$: 40 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{ mA}, I_B=0$	15			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	4.5			V
Collector cut-off current	I_{CBO}	$V_{CB}=20V, I_E=0$			0.4	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=2V, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=1V, I_C=10\text{ mA}$	40		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=15\text{ mA}, I_B=1.5\text{ mA}$			0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=15\text{ mA}, I_B=1.5\text{ mA}$			1.2	V
Transition frequency	f_T	$V_{CE}=10V, I_C=10\text{ mA}$ $f=100\text{ MHz}$	500			MHz